

RB706F-40

PRV : 45 Volts

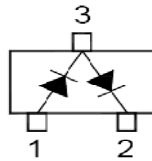
I_o : 30 mA

FEATURES :

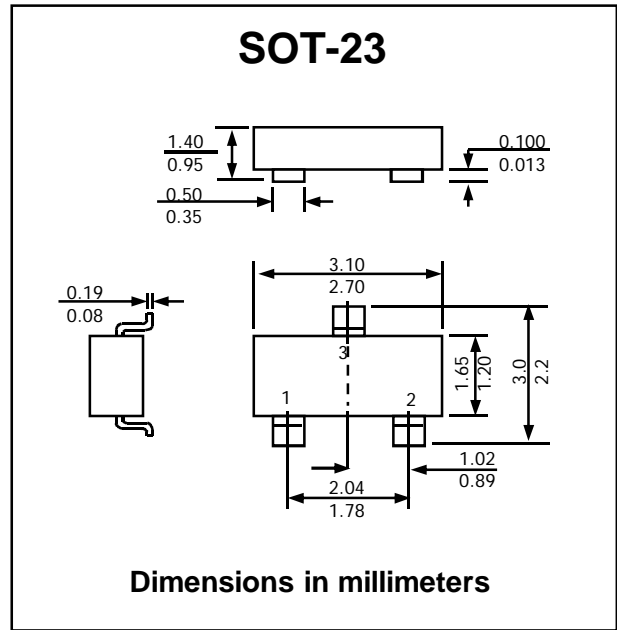
- * Small surface mounting type
- * Low reverse current
- * High reliability
- * Pb / RoHS Free

MECHANICAL DATA :

- * Case : SOT-23 plastic Case
- * Marking Code : ZA



SILICON EPITAXIAL SCHOTTKY BARRIER DIODE



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	VALUE	Unit
Repetitive Peak Reverse Voltage	V _{RM}	45	V
Reverse Voltage	V _R	40	V
Average Rectified Forward Current	I _{F(AV)}	30	mA
Peak Forward Surge Current (t = 8.3 ms)	I _{FSM}	200	mA
Junction Temperature	T _J	125	°C
Storage temperature range	T _{STG}	-55 to + 125	°C

Electrical Characteristics (T_a = 25 °C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Forward Voltage	V _F	I _F = 1 mA	-	-	0.37	V
Reverse Breakdown Voltage	V _{(BR)R}	I _R = 10 μA	45	-	-	V
Reverse Current	I _R	V _R = 10 V	-	-	1	μA
Capacitance between terminals	C _T	V _R = 1 V, f = 1MHz	-	2.0	-	pF

RATING AND CHARACTERISTIC CURVES (RB706F-40)

